

### < C band internally matched power GaAs FET >

# **MGFC42V6472A**

6.4 - 7.2 GHz BAND / 16W

#### **DESCRIPTION**

The MGFC42V6472A is an internally impedance-matched GaAs power FET especially designed for use in 6.4-7.2 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

#### **FEATURES**

Internally matched to 50(ohm) system

High output power

P1dB=16W (TYP.) @f=6.4 - 7.2GHz

• High power gain

GLP=8.0dB (TYP.) @f=6.4 - 7.2GHz

• High power added efficiency

P.A.E.=31% (TYP.) @f=6.4 - 7.2GHz

• Low distortion [item -51]

IM3=-45dBc (TYP.) @Po=31.0dBm S.C.L

#### **APPLICATION**

• item 01: 6.4 - 7.2 GHz band power amplifier

• item 51: 6.4 - 7.2 GHz band digital radio communication

#### **QUALITY**

• IG

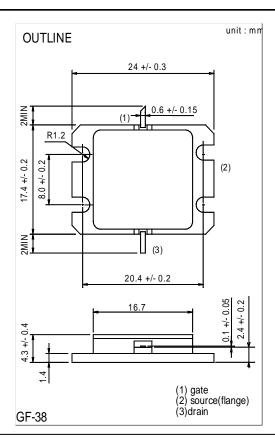
#### RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=4.5A • RG=25ohm Refer to Bias Procedure

### Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit			
VGDO	Gate to drain breakdown voltage	-15	V			
VGSO	Gate to source breakdown voltage	-15	V			
ID	Drain current	15	Α			
IGR	Reverse gate current	-40	mA			
IGF	Forward gate current	84	mA			
PT *1	Total power dissipation	93.7	W			
Tch	Cannel temperature	175	°C			
Tstg	Storage temperature	-65 to +175	°C			
*1 · Tc_25°C						

\*1 : Tc=25°C



Keep Safety first in your circuit designs! Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measure such as (I) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

### Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	9	12	Α
gm	Transconductance	VDS=3V,ID=4.4A	-	4	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=80mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=4.5A	41.5	42.5	-	dBm
GLP	Linear Power Gain	f=6.4 – 7.2GHz	7	8	-	dB
ID	Drain current		-	4.5	-	Α
P.A.E.	Power added efficiency		-	31	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	=	1.6	°C/W

<sup>\*2 :</sup>item -51 ,2 tone test,Po=31.0dBm Single Carrier Level ,f=7.2GHz,delta f=10MHz

<sup>\*3:</sup> Channel-case

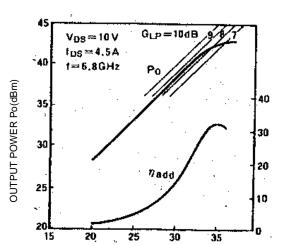
### MGFC42V6472A TYPICAL CHARACTERISTICS (Ta=25deg.C)

P1dB,Glp VS. f

 $V_{DS} = 10(V)$ los=4.5(A) OUTPUT POWER P1dB(dBm) 42 GLP 41

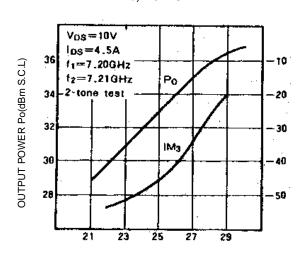
6.4 6.5 6.6 6.7 6.8 6.9 7.0 7.1

Po,Eadd VS. Pin



POWER ADDED EFFICIENCY Eadd(%)

Po,IM3 VS. Pin



IM3(dBc)

LINEAR POWER GAIN GIp(dB)

### **MGFC42V6472A S-parameters**( Ta=25deg.C , VDS=10(V),IDS=4.5(A) )

	S Parameters (TYP.)							
f	S <sub>11</sub>		S	21	S <sub>12</sub>		S <sub>22</sub>	
(GHz)	Magn.	Angle(deg.)	Magn.	Angle(deg.)	Magn.	Angle(deg.)	Magn.	Angle(deg.)
6.40	0.41	77	2.83	-95	0.068	-147	0.30	67
6.50	0.40	59	2.80	-111	0.072	-162	0.35	59
6.60	0.38	42	2.78	-127	0.075	-177	0.40	54
6.70	0.36	26	2.72	-143	0.078	167	0.42	48
6.80	0.33	11	2.64	-158	0.080	151	0.44	42
6.90	0.28	-3	2.60	-173	0.081	137	0.45	36
7.00	0.22	-20	2.57	171	0.082	122	0.44	32
7.10	0.17	-46	2.53	157	0.084	108	0.43	28
7.20	0.14	-91	2.50	141	0.086	93	0.40	26

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